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FPF2G120BF07ASP F2, 3ch Boost module PCM and NTC

General Description

The FPF2G120BF07ASP is the 3ch boost topology which is providing an optimized solution for the multi-string solar application. And the integrated high speed field stop IGBTs and SiC diodes are providing lower conduction and switching losses. And the pre-applied PCM requires no additional process of the thermal interface material printing. Furthermore, the screw clamp provides a fast and reliable mounting method.

Electrical Features

- High Efficiency
- Low Conduction and Switching Losses
- High Speed Field Stop IGBT
- SiC SBD for Boost Diode
- Built-in NTC for Temperature Monitoring

Mechanical Features

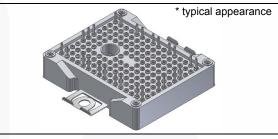
- Compact Size : F2 Package
- Soldering Pin
- Al₂O₃ Substrate with Low Thermal Resistance
- Pre-applied PCM (Phase Change Material)

Applications

Solar Inverter

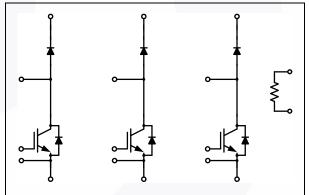
Related Materials

- AN-5077: Design Considerations for High Power Module (HPM)
- AN-4186: F1 and F2 Modules with Pre-applied Phase Change Material (PCM)



June 2015





Internal Circuit Diagram

Package Marking and Ordering Information

Device	Device Marking	Package	PCM	Packing Type	Quantity / Tray
FPF2G120BF07AS	FPF2G120BF07AS	F2	Х	Tray	14
FPF2G120BF07ASP	FPF2G120BF07ASP	F2	0	Tray	14

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FPF2G120BF07ASP - F2, 3ch Boost module PCM and NTC

Symbol	Description	Condition	Rating	Units
Boost IGB1	-			·
V _{CES}	Collector-Emitter Voltage		650	V
V _{GES}	Gate-Emitter Voltage	± 20	V	
	Transient Gate-Emitter Voltage		± 25	V
I _C	Continuous Collector Current	T _C = 80 °C, T _{Jmax} = 175 °C	40	A
I _{CM}	Pulsed Collector Current	limited by T _{Jmax}	80	A
P _D	Maximum Power Dissipation		156	W
TJ	Operating Junction Temperature		- 40 to + 150	°C
Protection	Diode			1
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
IF	Continuous Forward Current	T _C = 80 °C, T _{Jmax} = 175 °C	15	A
I _{FM}	Maximum Forward Current		30	A
I _{FSM}	Non-repetitive Peak Surge Current	60Hz Single Half-Sine Wave	150	A
l ² t - value	Surge Current Integral Value		93	A ² s
PD	Maximum Power Dissipation		140	W
TJ	Operating Junction Temperature		- 40 to + 150	°C
Boost Diod	e			
V _{RRM}	Peak Repetitive Reverse Voltage		650	V
l _F	Continuous Forward Current	T _C = 80 °C, T _{Jmax} = 175 °C	15	A
I _{FM}	Maximum Forward Current		30	A
I _{FSM}	Non-repetitive Peak Surge Current	60Hz Single Half-Sine Wave	120	Α
l ² t - value	Surge Current Integral Value		60	A ² s
P _D	Maximum Power Dissipation		98	W
TJ	Operating Junction Temperature		- 40 to + 150	°C
Module				
T _{STG}	Storage Temperature		- 40 to + 125	°C
V _{ISO}	Isolation Voltage	AC 1 min.	2500	V
IsoMaterial			Al ₂ O ₃	-
T _{MOUNT}	Mounting Torque		2.0 to 5.0	N•m
Creepage	Terminal to Heat Sink	11.5	mm	
	Terminal to Terminal	6.3	mm	
Clearance	Terminal to Heat Sink		10.0	mm
	Terminal to Terminal		5.0	mm

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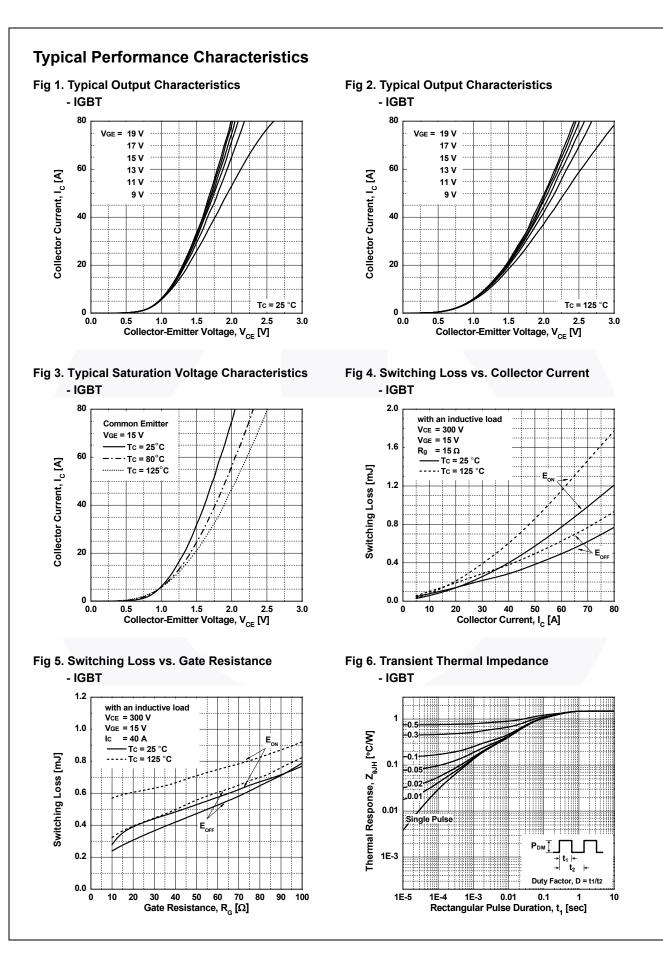
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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Boost IGE	ВТ		-	1		
Off Charac	teristics					
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA	650	-	-	V
ICES	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μA
I _{GES} On Charac	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	± 2	μA
V _{GE(th)}	Gate-Emitter Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 40 \text{ mA}$	3.9	5.1	6.8	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 40 A, V _{GE} = 15 V	-	1.55	2.2	V
()		$I_{\rm C}$ = 40 A, $V_{\rm GE}$ = 15 V, $T_{\rm C}$ = 125 °C	-	1.85	-	V
R _{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	3.3	-	mΩ
	Characteristics				1	
t _{d(on)}	Turn-On Delay Time	V _{CC} = 300 V	-	24	-	ns
t _r	Rise Time	$I_{\rm C} = 40$ A	-	24	-	ns
t _{d(off)}	Turn-Off Delay Time	V _{GE} = 15 V R _G = 15 Ω	-	132	-	ns
t _f	Fall Time	Inductive Load	-	17	-	ns
E _{ON}	Turn-On Switching Loss per Pulse	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$	-	0.40	-	mJ
E _{OFF}	Turn-Off Switching Loss per Pulse		-	0.28	-	mJ
t _{d(on)}	Turn-On Delay Time	V _{CC} = 300 V	-	22	-	ns
t _r	Rise Time	$I_{\rm C} = 40$ A	-	27	-	ns
t _{d(off)}	Turn-Off Delay Time	V _{GE} = 15 V R _G = 15 Ω	-	148	-	ns
t _f	Fall Time	Inductive Load	-	17	-	ns
E _{ON}	Turn-On Switching Loss per Pulse	T _C = 125 °C	-	0.59	-	mJ
E _{OFF}	Turn-Off Switching Loss per Pulse		-	0.37	-	mJ
Qg	Total Gate Charge	V _{CC} = 300 V, I _C = 40 A, V _{GE} = 15 V	-	65	-	nC
R _{0JC}	Thermal Resistance of Junction to Case	per Chip	-	-	0.96	°C/W
R _{0CH}	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.54	-	°C/W
Protectio	n Diode				1	
V _F	Diode Forward Voltage	I _F = 15 A	-	1.05	1.4	V
. 6		I _F = 15 A, T _C = 125 °C	· ·	0.95	-	V
R _{LEAD}	Lead Resistance of Pin to Chip	per Chip	-	2.4	-	mΩ
I _R	Reverse Leakage Current	$V_{\rm R} = 650 \text{ V}$	-	-	250	μΑ
R _{θJC}	Thermal Resistance of Junction to Case	per Chip	-	-	1.07	°C/W
R _{0CH}	Thermal Resistance of Case to Heat sink	per Chip, λ_{PCM} = 3.4 W/mK	-	0.33	-	°C/W
Boost Dic						
V _F	Diode Forward Voltage	I _F = 15 A	-	1.45	1.9	V
۷F	Didde Forward Voltage	I _F = 15 A, T _C = 125 °C	-	1.45	1.9	V
D	Lead Resistance of Pin to Chip	$r_F = 15 \text{ A}, r_C = 123 \text{ C}$		2.8	-	
R _{LEAD}	Reverse Leakage Current	$V_{\rm R} = 650 \text{ V}$	-	2.0	- 60	mΩ μA
I _R I	Reverse Recovery Current	V _R = 300 V, I _F = 15 A,		9.2	00	A
	Total Capacitive Charge	$v_R = 300 v_1 F = 13 A_1$ di / dt = 1390 A/us,	-	9.2 60	-	nC
Q _C	Reverse Recovery Energy	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$		4.9		
E _{rec}	Reverse Recovery Energy	V _R = 300 V, I _F = 15 A,		4.9 9.2	-	μJ
I _{rr}	Total Capacitive Charge	$v_R = 300 \text{ V}, \text{ I}_F = 13 \text{ A},$ di / dt = 1390 A/us,	-	9.2 65	-	A nC
Q _C	Reverse Recovery Energy	$T_{\rm C} = 125 \ ^{\circ}{\rm C}$		4.9	-	
E _{rec}	Thermal Resistance of Junction to Case	per Chip	-	4.9	- 1.52	μJ °C/W
R _{θJC} R _{θCH}	Thermal Resistance of Case to Heat sink	per Chip, λ _{PCM} = 3.4 W/mK	-	- 0.18	1.52	°C/W

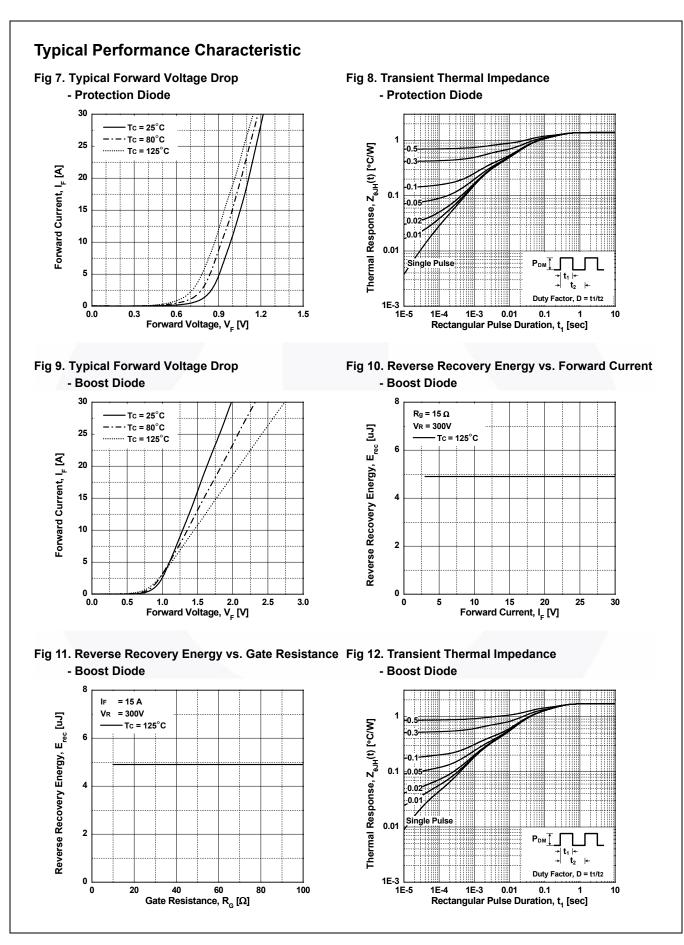
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Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
NTC (The	rmistor)					
NIC	Rated Resistance	T _C = 25 °C	-	10	-	kΩ
		T _C = 100 °C	-	936	-	Ω
	Tolerance	T _C = 25 °C	- 3	-	+ 3	%
P _D	Power Dissipation	T _C = 25 °C	-	-	20	mW
B _{Value}	B-Constant	B _{25/50}	-	3450	-	K
		B _{25/100}	-	3513	-	K

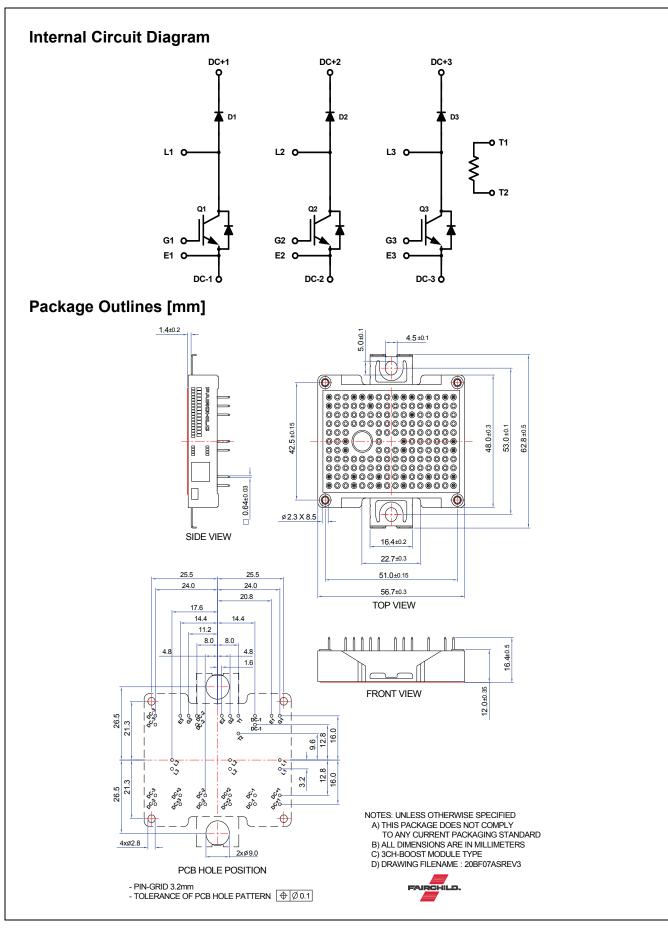
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